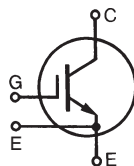


600V XPT™ IGBT
GenX3™
IXYN150N60B3

 Extreme Light Punch through
 IGBT for 10-30kHz Switching


$$V_{CES} = 600V$$

$$I_{C110} = 140A$$

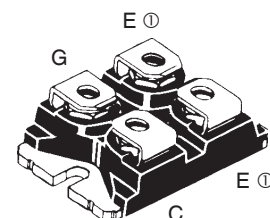
$$V_{CE(sat)} \leq 2.20V$$

$$t_{fi(typ)} = 80ns$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	600	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	250	A
I_{LRMS}	Terminal Current Limit	200	A
I_{C110}	$T_C = 110^\circ C$	140	A
I_{CM}	$T_C = 25^\circ C$, 1ms	750	A
I_A	$T_C = 25^\circ C$	75	A
E_{AS}	$T_C = 25^\circ C$	1	J
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 300$ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ C$ $R_G = 82\Omega$, Non Repetitive	8	μs
P_C	$T_C = 25^\circ C$	830	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
V_{ISOL}	50/60Hz $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	2500 3000 V~ V~
M_d	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in Nm/lb.in
Weight		30	g

SOT-227B, miniBLOC

E153432



G = Gate, C = Collector, E = Emitter
 Ⓣ either emitter terminal can be used as
 Main or Kelvin Emitter

Features

- Optimized for Low Conduction and Switching Losses
- miniBLOC, with Aluminium Nitride Isolation
- International Standard Package
- Isolation Voltage 2500V~
- Optimized for 10-30kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

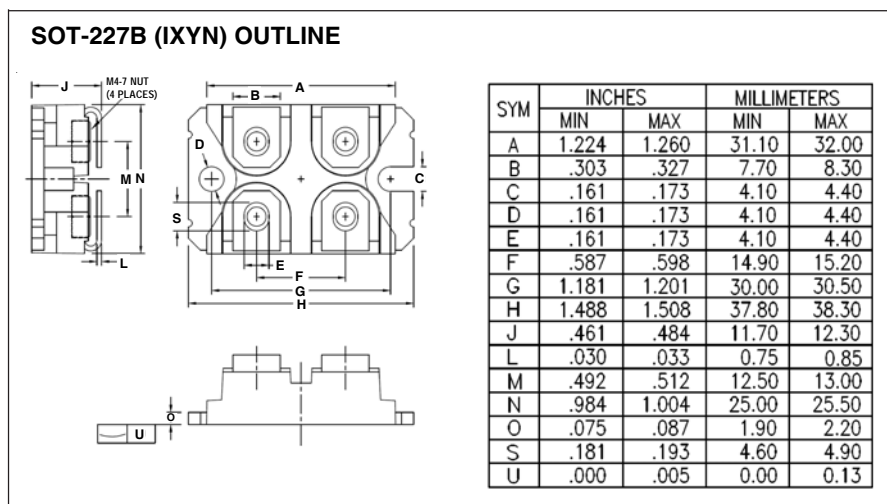
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			10 μA 1 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = 150A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		1.77 2.10	V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	40	70	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		6950	pF
C_{oes}			400	pF
C_{res}			150	pF
$Q_{g(on)}$	$I_C = 150\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		260	nC
Q_{ge}			39	nC
Q_{gc}			115	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 75\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		27	ns
t_{ri}			88	ns
E_{on}			4.20	mJ
$t_{d(off)}$			167	ns
t_{fi}			80	ns
E_{off}			2.60	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 75\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		26	ns
t_{ri}			84	ns
E_{on}			5.30	mJ
$t_{d(off)}$			220	ns
t_{fi}			110	ns
E_{off}			3.76	mJ
R_{thJC}				0.18 $^\circ\text{C/W}$
R_{thCS}		0.05		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .



PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

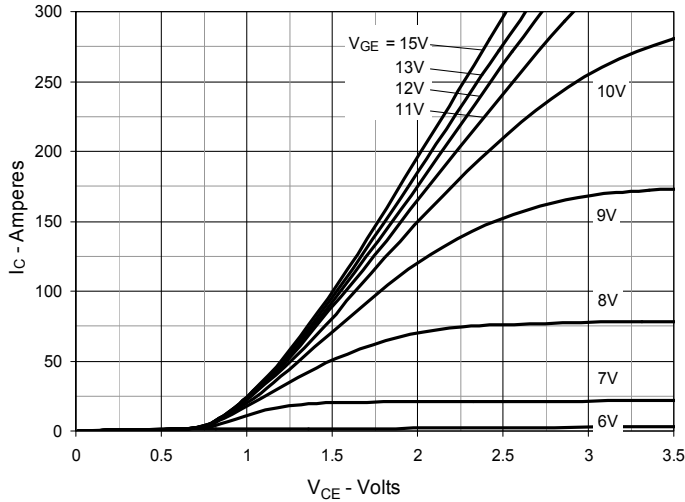
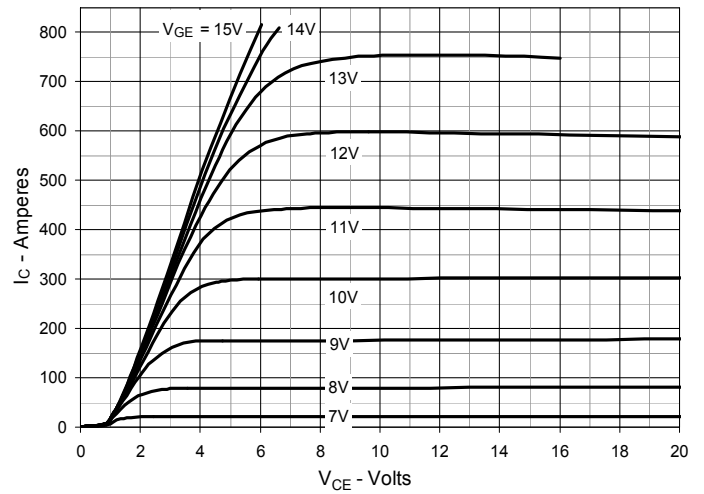
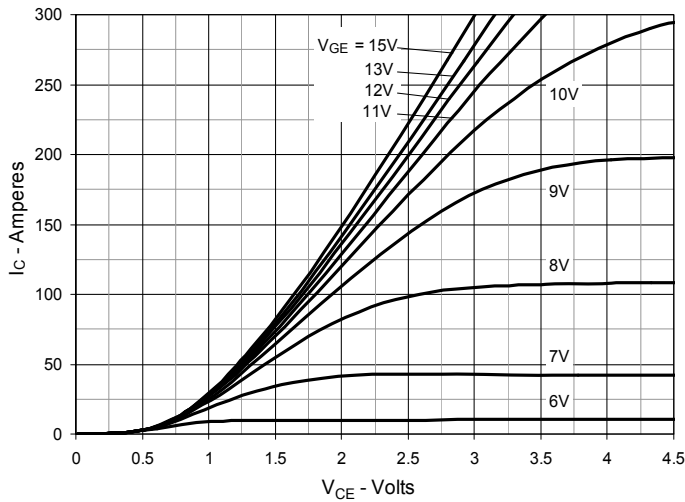
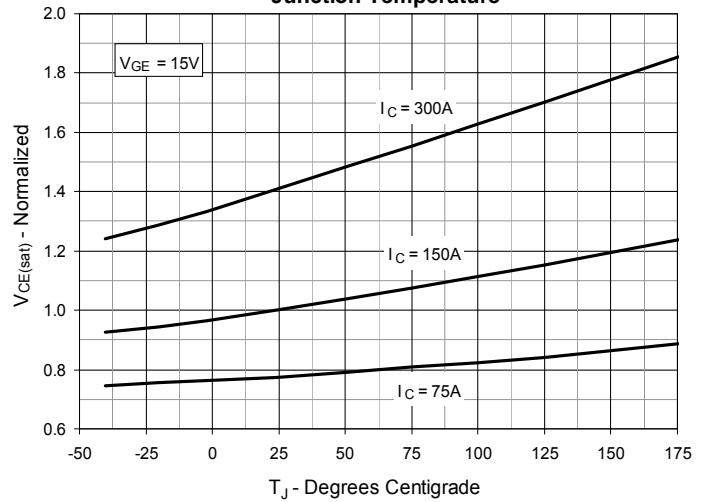
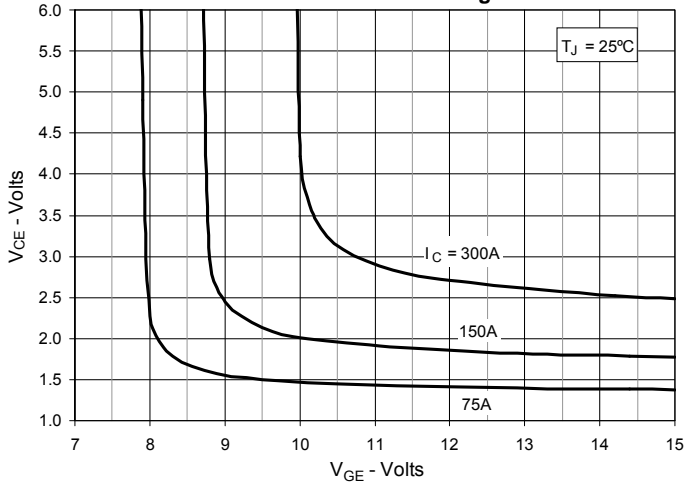
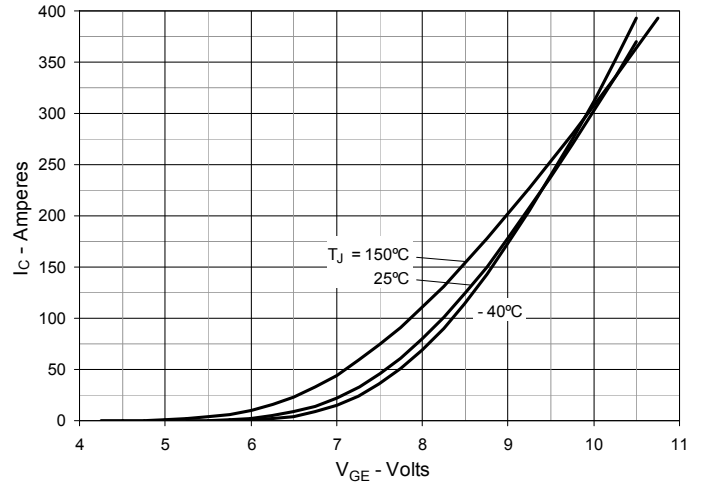
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


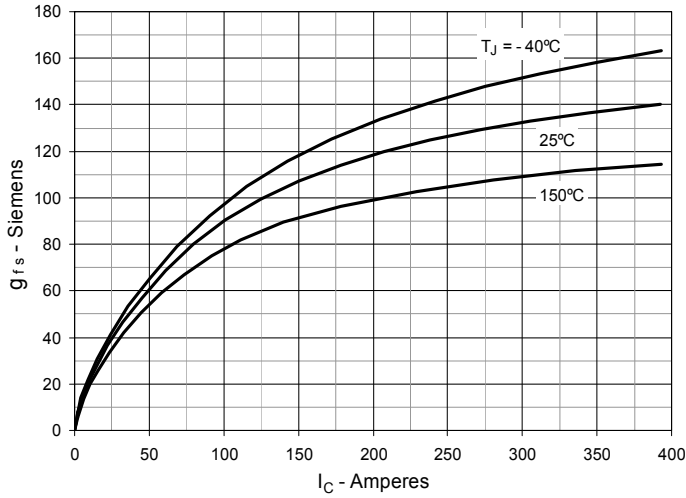
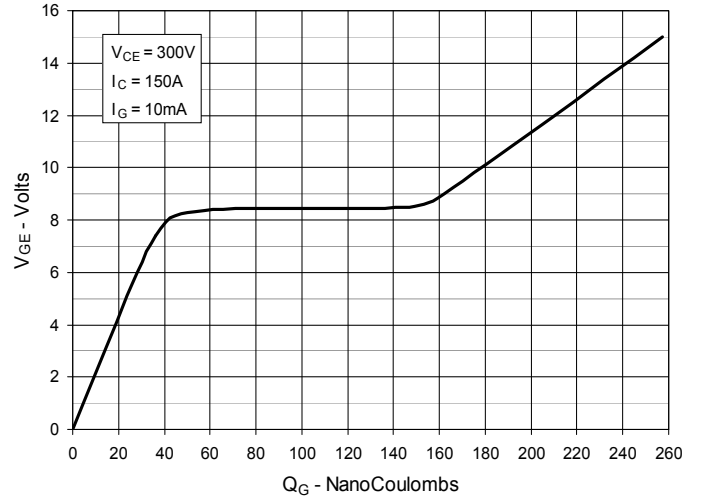
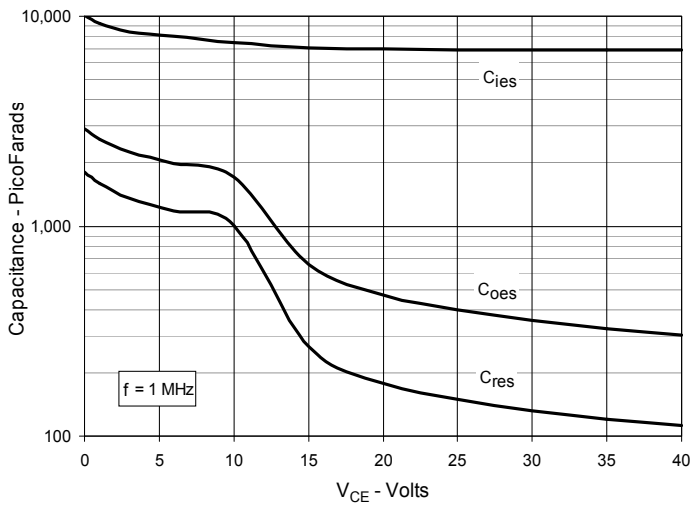
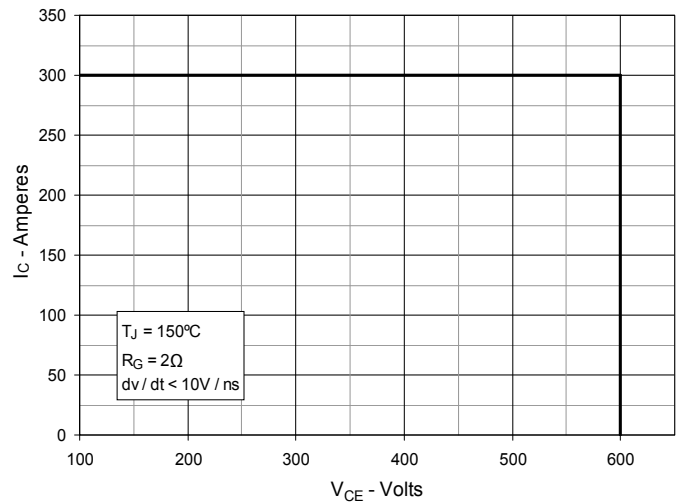
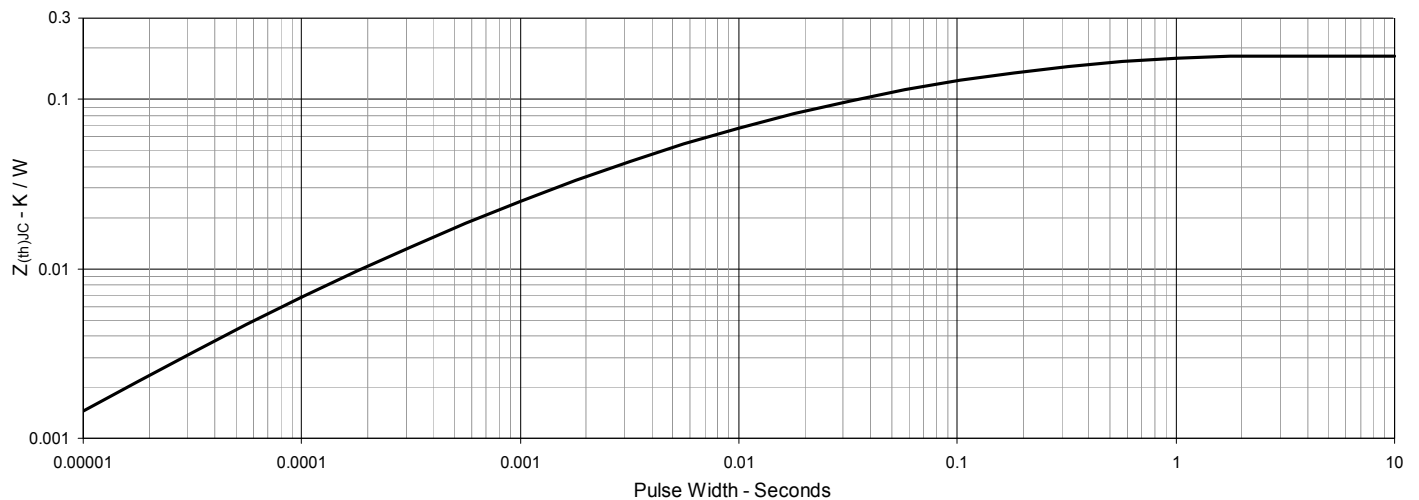
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


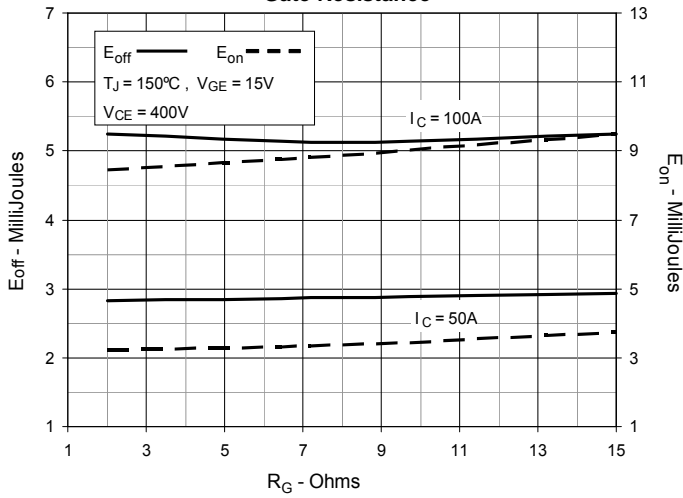
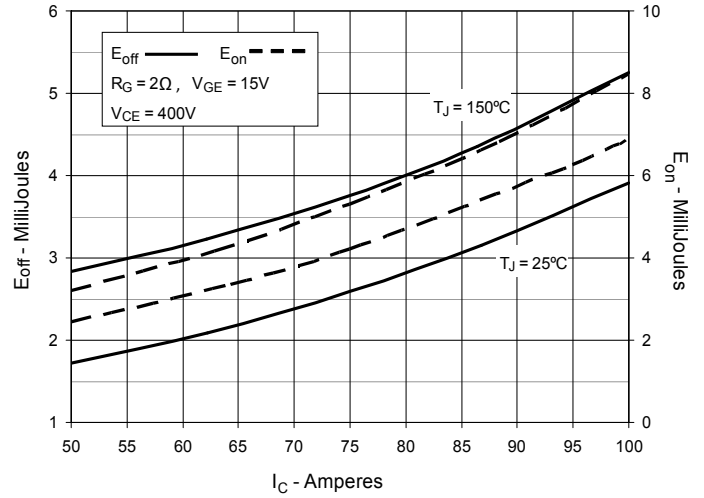
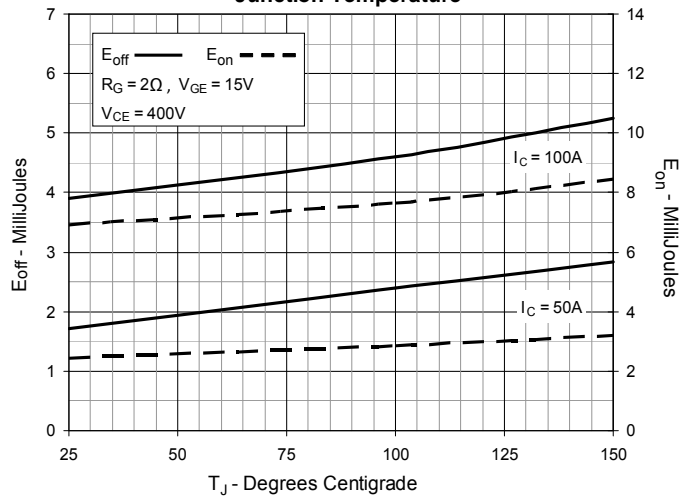
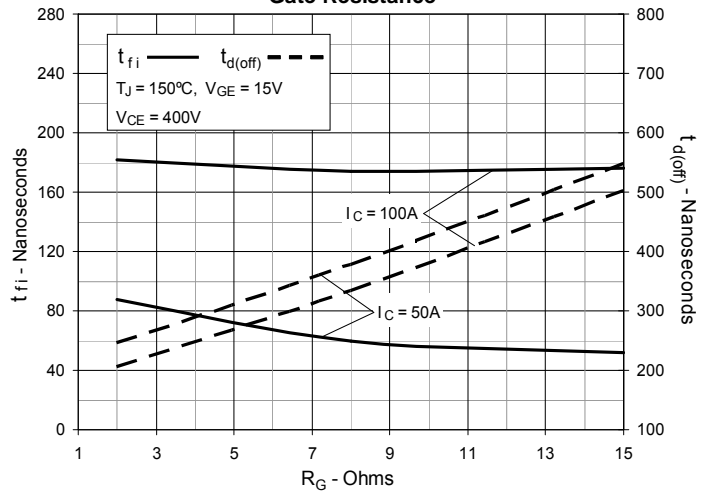
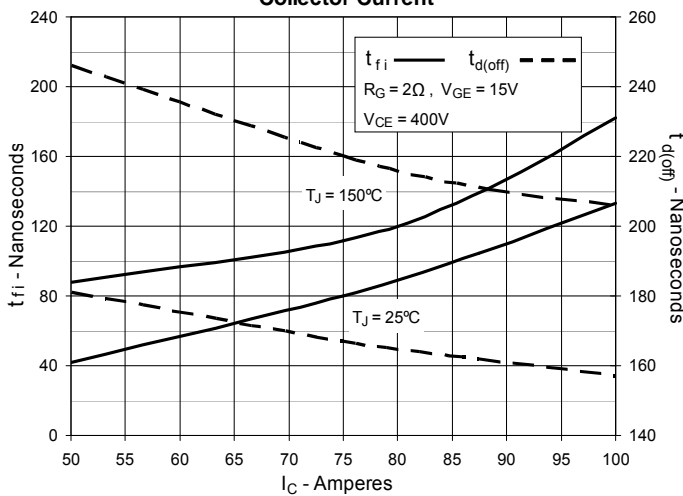
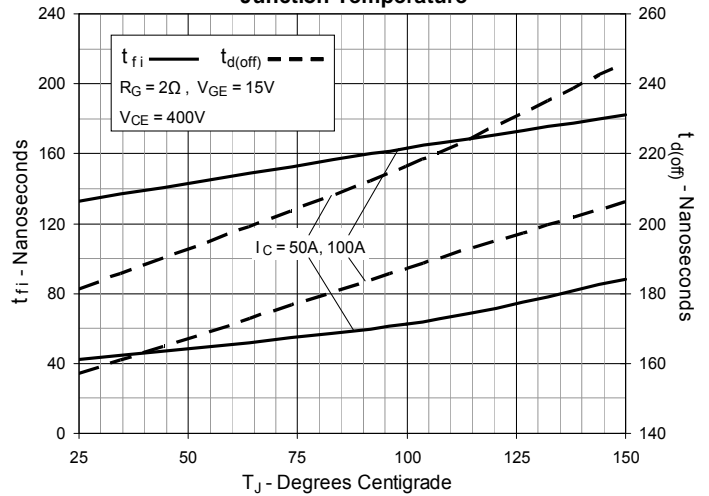
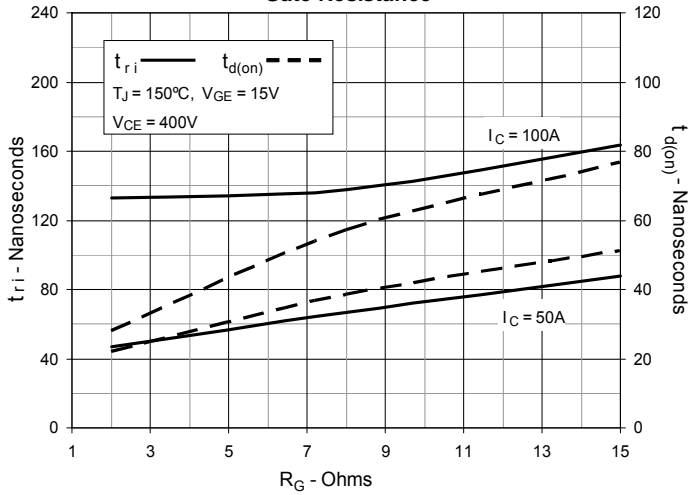
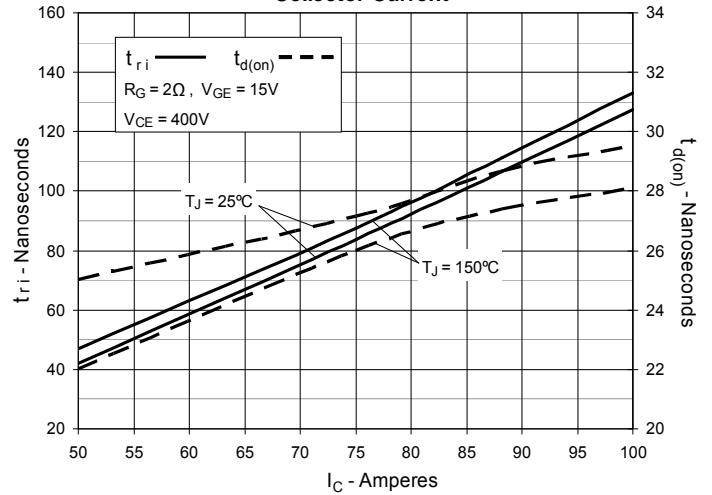
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature
